



Welcome to [E-XFL.COM](https://www.e-xfl.com)

Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	125
Number of Gates	24000
Voltage - Supply	3V ~ 3.6V, 4.75V ~ 5.25V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	160-BQFP
Supplier Device Package	160-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a42mx16-3pqg160

Contents

1	Revision History	1
1.1	Revision 15.0	1
1.2	Revision 14.0	1
1.3	Revision 13.0	1
1.4	Revision 12.0	1
1.5	Revision 11.0	1
1.6	Revision 10.0	1
1.7	Revision 9.0	2
1.8	Revision 6.0	2
2	40MX and 42MX FPGA Families	1
2.1	Features	1
2.1.1	High Capacity	1
2.1.2	High Performance	1
2.1.3	HiRel Features	1
2.1.4	Ease of Integration	1
2.2	Product Profile	1
2.3	Ordering Information	3
2.4	Plastic Device Resources	4
2.5	Ceramic Device Resources	4
2.6	Temperature Grade Offerings	5
2.7	Speed Grade Offerings	5
3	40MX and 42MX FPGAs	6
3.1	General Description	6
3.2	MX Architectural Overview	6
3.2.1	Logic Modules	6
3.2.2	Dual-Port SRAM Modules	8
3.2.3	Routing Structure	9
3.2.4	Clock Networks	10
3.2.5	MultiPlex I/O Modules	11
3.3	Other Architectural Features	12
3.3.1	Performance	12
3.3.2	User Security	12
3.3.3	Programming	12
3.3.4	Power Supply	13
3.3.5	Power-Up/Down in Mixed-Voltage Mode	13
3.3.6	Transient Current	13
3.3.7	Low Power Mode	14
3.4	Power Dissipation	14
3.4.1	General Power Equation	14
3.4.2	Static Power Component	14
3.4.3	Active Power Component	14
3.4.4	Equivalent Capacitance	15
3.4.5	C _{EQ} Values for Microsemi MX FPGAs	15
3.4.6	Test Circuitry and Silicon Explorer II Probe	16
3.4.7	Design Consideration	17
3.4.8	IEEE Standard 1149.1 Boundary Scan Test (BST) Circuitry	17
3.4.9	JTAG Mode Activation	19
3.4.10	TRST Pin and TAP Controller Reset	19

3.4.11	Boundary Scan Description Language (BSDL) File	19
3.5	Development Tool Support	19
3.6	Related Documents	20
3.6.1	Application Notes	20
3.6.2	User Guides and Manuals	20
3.6.3	Miscellaneous	20
3.7	5.0 V Operating Conditions	20
3.7.1	5 V TTL Electrical Specifications	21
3.8	3.3 V Operating Conditions	22
3.8.1	3.3 V LVTTTL Electrical Specifications	23
3.9	Mixed 5.0 V / 3.3 V Operating Conditions (for 42MX Devices Only)	23
3.9.1	Mixed 5.0V/3.3V Electrical Specifications	25
3.9.2	Output Drive Characteristics for 5.0 V PCI Signaling	25
3.9.3	Output Drive Characteristics for 3.3 V PCI Signaling	27
3.9.4	Junction Temperature (T_J)	28
3.9.5	Package Thermal Characteristics	28
3.10	Timing Models	30
3.10.1	Parameter Measurement	32
3.10.2	Sequential Module Timing Characteristics	34
3.10.3	Sequential Timing Characteristics	34
3.10.4	Decode Module Timing	35
3.10.5	SRAM Timing Characteristics	35
3.10.6	Dual-Port SRAM Timing Waveforms	35
3.10.7	Predictable Performance: Tight Delay Distributions	37
3.11	Timing Characteristics	37
3.11.1	Critical Nets and Typical Nets	37
3.11.2	Long Tracks	37
3.11.3	Timing Derating	38
3.11.4	Temperature and Voltage Derating Factors	38
3.11.5	PCI System Timing Specification	40
3.11.6	PCI Models	40
3.12	Pin Descriptions	83
4	Package Pin Assignments	86

Figures

Figure 1	Ordering Information	3
Figure 2	42MX C-Module Implementation	7
Figure 3	42MX C-Module Implementation	7
Figure 4	42MX S-Module Implementation	8
Figure 5	A42MX24 and A42MX36 D-Module Implementation	9
Figure 6	A42MX36 Dual-Port SRAM Block	9
Figure 7	MX Routing Structure	10
Figure 8	Clock Networks of 42MX Devices	11
Figure 9	Quadrant Clock Network of A42MX36 Devices	11
Figure 10	42MX I/O Module	12
Figure 11	PCI Output Structure of A42MX24 and A42MX36 Devices	12
Figure 12	Silicon Explorer II Setup with 40MX	16
Figure 13	Silicon Explorer II Setup with 42MX	17
Figure 14	42MX IEEE 1149.1 Boundary Scan Circuitry	18
Figure 15	Device Selection Wizard	19
Figure 16	Typical Output Drive Characteristics (Based Upon Measured Data)	28
Figure 17	40MX Timing Model*	30
Figure 18	42MX Timing Model	30
Figure 19	42MX Timing Model (Logic Functions Using Quadrant Clocks)	31
Figure 20	42MX Timing Model (SRAM Functions)	32
Figure 21	Output Buffer Delays	32
Figure 22	AC Test Loads	33
Figure 23	Input Buffer Delays	33
Figure 24	Module Delays	33
Figure 25	Flip-Flops and Latches	34
Figure 26	Input Buffer Latches	34
Figure 27	Output Buffer Latches	35
Figure 28	Decode Module Timing	35
Figure 29	SRAM Timing Characteristics	35
Figure 30	42MX SRAM Write Operation	36
Figure 31	42MX SRAM Synchronous Read Operation	36
Figure 32	42MX SRAM Asynchronous Read Operation—Type 1 (Read Address Controlled)	36
Figure 33	42MX SRAM Asynchronous Read Operation—Type 2 (Write Address Controlled)	37
Figure 34	42MX Junction Temperature and Voltage Derating Curves (Normalized to $T_J = 25^\circ\text{C}$, $V_{CCA} = 5.0\text{ V}$)	38
Figure 35	40MX Junction Temperature and Voltage Derating Curves (Normalized to $T_J = 25^\circ\text{C}$, $V_{CC} = 5.0\text{ V}$)	39
Figure 36	42MX Junction Temperature and Voltage Derating Curves (Normalized to $T_J = 25^\circ\text{C}$, $V_{CCA} = 3.3\text{ V}$)	39
Figure 37	40MX Junction Temperature and Voltage Derating Curves (Normalized to $T_J = 25^\circ\text{C}$, $V_{CC} = 3.3\text{ V}$)	40
Figure 38	PL44	86
Figure 39	PL68	88
Figure 40	PL84	90
Figure 41	PQ100	93
Figure 42	PQ144	97
Figure 43	PQ160	102
Figure 44	PQ208	107
Figure 45	PQ240	113
Figure 46	VQ80	120
Figure 47	VQ100	123
Figure 48	TQ176	126
Figure 49	CQ208	131
Figure 50	CQ256	138

3.3.7 Low Power Mode

42MX devices have been designed with a Low Power Mode. This feature, activated with setting the special LP pin to HIGH for a period longer than 800 ns, is particularly useful for battery-operated systems where battery life is a primary concern. In this mode, the core of the device is turned off and the device consumes minimal power with low standby current. In addition, all input buffers are turned off, and all outputs and bidirectional buffers are tristated. Since the core of the device is turned off, the states of the registers are lost. The device must be re-initialized when exiting Low Power Mode. I/Os can be driven during LP mode, and clock pins should be driven HIGH or LOW and should not float to avoid drawing current. To exit LP mode, the LP pin must be pulled LOW for over 200 μ s to allow for charge pumps to power up, and device initialization will begin.

3.4 Power Dissipation

The general power consumption of MX devices is made up of static and dynamic power and can be expressed with the following equation.

3.4.1 General Power Equation

$$P = [ICC_{\text{standby}} + ICC_{\text{active}}] \cdot V_{CCI} + I_{OL} \cdot V_{OL} \cdot N + I_{OH} \cdot (V_{CCI} - V_{OH}) \cdot M$$

EQ 1

where:

- ICC_{standby} is the current flowing when no inputs or outputs are changing.
- ICC_{active} is the current flowing due to CMOS switching.
- I_{OL} , I_{OH} are TTL sink/source currents.
- V_{OL} , V_{OH} are TTL level output voltages.
- N equals the number of outputs driving TTL loads to V_{OL} .
- M equals the number of outputs driving TTL loads to V_{OH} .

Accurate values for N and M are difficult to determine because they depend on the family type, on design details, and on the system I/O. The power can be divided into two components: static and active.

3.4.2 Static Power Component

The static power due to standby current is typically a small component of the overall power consumption. Standby power is calculated for commercial, worst-case conditions. The static power dissipation by TTL loads depends on the number of outputs driving, and on the DC load current. For instance, a 32-bit bus sinking 4mA at 0.33V will generate 42mW with all outputs driving LOW, and 140mW with all outputs driving HIGH. The actual dissipation will average somewhere in between, as I/Os switch states with time.

3.4.3 Active Power Component

Power dissipation in CMOS devices is usually dominated by the dynamic power dissipation. Dynamic power consumption is frequency-dependent and is a function of the logic and the external I/O. Active power dissipation results from charging internal chip capacitances of the interconnect, unprogrammed antifuses, module inputs, and module outputs, plus external capacitances due to PC board traces and load device inputs. An additional component of the active power dissipation is the totem pole current in the CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent active power dissipation.

The power dissipated by a CMOS circuit can be expressed by the equation:

$$\text{Power}(\mu\text{W}) = C_{EQ} \cdot V_{CCA}^2 \cdot F(1)$$

EQ 2

where:

- C_{EQ} = Equivalent capacitance expressed in picofarads (pF)

3. All outputs unloaded. All inputs = VCC/VCCI or GND

3.8 3.3 V Operating Conditions

The following table shows 3.3 V operating conditions.

Table 16 • Absolute Maximum Ratings for 40MX Devices*

Symbol	Parameter	Limits	Units
VCC	DC Supply Voltage	–0.5 to +7.0	V
VI	Input Voltage	–0.5 to VCC + 0.5	V
VO	Output Voltage	–0.5 to VCC + 0.5	V
t _{STG}	Storage Temperature	–65 to +150	°C

Note: *Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Devices should not be operated outside the recommended operating conditions.

Table 17 • Absolute Maximum Ratings for 42MX Devices*

Symbol	Parameter	Limits	Units
VCCI	DC Supply Voltage for I/Os	–0.5 to +7.0	V
VCCA	DC Supply Voltage for Array	–0.5 to +7.0	V
VI	Input Voltage	–0.5 to VCCI+0.5	V
VO	Output Voltage	–0.5 to VCCI+0.5	V
t _{STG}	Storage Temperature	–65 to +150	°C

Note: *Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Devices should not be operated outside the recommended operating conditions.

Table 18 • Recommended Operating Conditions

Parameter	Commercial	Industrial	Military	Units
Temperature Range*	0 to +70	–40 to +85	–55 to +125	°C
VCC (40MX)	3.0 to 3.6	3.0 to 3.6	3.0 to 3.6	V
VCCA (42MX)	3.0 to 3.6	3.0 to 3.6	3.0 to 3.6	V
VCCI (42MX)	3.0 to 3.6	3.0 to 3.6	3.0 to 3.6	V

Note: *Ambient temperature (T_A) is used for commercial and industrial grades; case temperature (T_C) is used for military grades.

All the following tables show various specifications and operating conditions of 40MX and 42MX FPGAs.

3.9.1 Mixed 5.0V/3.3V Electrical Specifications

Table 22 • Mixed 5.0V/3.3V Electrical Specifications

Symbol	Parameter	Commercial		Commercial –F		Industrial		Military		Units
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
VOH ¹	IOH = –10 mA	2.4		2.4						V
	IOH = –4 mA					2.4		2.4		V
VOL ¹	IOL = 10 mA	0.5		0.5						V
	IOL = 6 mA					0.4		0.4		V
VIL		–0.3	0.8	–0.3	0.8	–0.3	0.8	–0.3	0.8	V
VIH ²		2.0	VCCA + 0.3	2.0	VCCA + 0.3	2.0	VCCA + 0.3	2.0	VCCA + 0.3	V
IL	VIN = 0.5 V	–10		–10		–10		–10		μA
IH	VIN = 2.7 V	–10		–10		–10		–10		μA
Input Transition Time, T _R and T _F		500		500		500		500		ns
C _{IO} I/O Capacitance		10		10		10		10		pF
Standby Current, ICC ³	A42MX09	5		25		25		25		mA
	A42MX16	6		25		25		25		mA
	A42MX24, A42MX36	20		25		25		25		mA
Low Power Mode Standby Current		0.5		ICC – 5.0		ICC – 5.0		ICC – 5.0		mA
I/O I/O source sink current Can be derived from the <i>IBIS model</i> (http://www.microsemi.com/soc/techdocs/models/ibis.html)										

1. Only one output tested at a time. VCCI = min.

2. VIH(Min) is 2.4V for A42MX36 family. This applies only to VCCI of 5V and is not applicable to VCCI of 3.3V

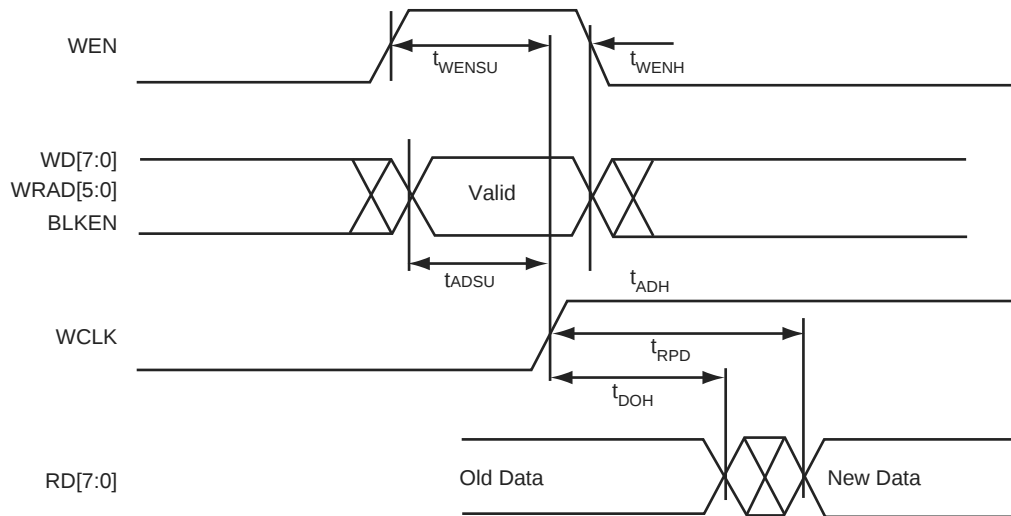
3. All outputs unloaded. All inputs = VCCI or GND

3.9.2 Output Drive Characteristics for 5.0 V PCI Signaling

MX PCI device I/O drivers were designed specifically for high-performance PCI systems. Figure 16, page 28 shows the typical output drive characteristics of the MX devices. MX output drivers are compliant with the PCI Local Bus Specification.

Table 23 • DC Specification (5.0 V PCI Signaling)¹

Symbol	Parameter	Condition	PCI		MX		Units
			Min.	Max.	Min.	Max.	
VCCI	Supply Voltage for I/Os		4.75	5.25	4.75	5.25 ²	V
VIH ³	Input High Voltage		2.0	VCC + 0.5	2.0	VCCI + 0.3	V
VIL	Input Low Voltage		–0.5	0.8	–0.3	0.8	V
IIH	Input High Leakage Current	VIN = 2.7 V		70	—	10	μA
IIL	Input Low Leakage Current	VIN=0.5 V		–70	—	–10	μA
VOH	Output High Voltage	IOUT = –2 mA IOUT = –6 mA	2.4		3.84		V
VOL	Output Low Voltage	IOUT = 3 mA, 6 mA		0.55	—	0.33	V

Figure 33 • 42MX SRAM Asynchronous Read Operation—Type 2 (Write Address Controlled)

3.10.7 Predictable Performance: Tight Delay Distributions

Propagation delay between logic modules depends on the resistive and capacitive loading of the routing tracks, the interconnect elements, and the module inputs being driven. Propagation delay increases as the length of routing tracks, the number of interconnect elements, or the number of inputs increases.

From a design perspective, the propagation delay can be statistically correlated or modeled by the fanout (number of loads) driven by a module. Higher fanout usually requires some paths to have longer routing tracks.

The MX FPGAs deliver a tight fanout delay distribution, which is achieved in two ways: by decreasing the delay of the interconnect elements and by decreasing the number of interconnect elements per path.

Microsemi's patented antifuse offers a very low resistive/capacitive interconnect. The antifuses, fabricated in 0.45 μm lithography, offer nominal levels of 100 Ω resistance and 7.0 fF capacitance per antifuse.

MX fanout distribution is also tight due to the low number of antifuses required for each interconnect path. The proprietary architecture limits the number of antifuses per path to a maximum of four, with 90 percent of interconnects using only two antifuses.

3.11 Timing Characteristics

Device timing characteristics fall into three categories: family-dependent, device-dependent, and design-dependent. The input and output buffer characteristics are common to all MX devices. Internal routing delays are device-dependent; actual delays are not determined until after place-and-route of the user's design is complete. Delay values may then be determined by using the Designer software utility or by performing simulation with post-layout delays.

3.11.1 Critical Nets and Typical Nets

Propagation delays are expressed only for typical nets, which are used for initial design performance evaluation. Critical net delays can then be applied to the most timing critical paths. Critical nets are determined by net property assignment in Microsemi's Designer software prior to placement and routing. Up to 6% of the nets in a design may be designated as critical.

3.11.2 Long Tracks

Some nets in the design use long tracks, which are special routing resources that span multiple rows, columns, or modules. Long tracks employ three and sometimes four antifuse connections, which increase capacitance and resistance, resulting in longer net delays for macros connected to long tracks. Typically, up to 6 percent of nets in a fully utilized device require long tracks. Long tracks add

Table 35 • A40MX02 Timing Characteristics (Nominal 3.3 V Operation) (continued)
(Worst-Case Commercial Conditions, VCC = 3.0 V, T_J = 70°C)

Parameter / Description			–3 Speed		–2 Speed		–1 Speed		Std Speed		–F Speed		Units
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t _{RD1}	FO = 1 Routing Delay			2.0		2.2		2.5		3.0		4.2	ns
t _{RD2}	FO = 2 Routing Delay			2.7		3.1		3.5		4.1		5.7	ns
t _{RD3}	FO = 3 Routing Delay			3.4		3.9		4.4		5.2		7.3	ns
t _{RD4}	FO = 4 Routing Delay			4.2		4.8		5.4		6.3		8.9	ns
t _{RD8}	FO = 8 Routing Delay			7.1		8.2		9.2		10.9		15.2	ns
Logic Module Sequential Timing²													
t _{SUD}	Flip-Flop (Latch) Data Input Set-Up		4.3		4.9		5.6		6.6		9.2		ns
t _{HD} ³	Flip-Flop (Latch) Data Input Hold		0.0		0.0		0.0		0.0		0.0		ns
t _{SUENA}	Flip-Flop (Latch) Enable Set-Up		4.3		4.9		5.6		6.6		9.2		ns
t _{HENA}	Flip-Flop (Latch) Enable Hold		0.0		0.0		0.0		0.0		0.0		ns
t _{WCLKA}	Flip-Flop (Latch) Clock Active Pulse Width		4.6		5.3		6.0		7.0		9.8		ns
t _{WASYN}	Flip-Flop (Latch) Asynchronous Pulse Width		4.6		5.3		6.0		7.0		9.8		ns
t _A	Flip-Flop Clock Input Period		6.8		7.8		8.9		10.4		14.6		ns
f _{MAX}	Flip-Flop (Latch) Clock Frequency (FO = 128)			109		101		92		80		48	MHz
Input Module Propagation Delays													
t _{INYH}	Pad-to-Y HIGH			1.0		1.1		1.3		1.5		2.1	ns
t _{INYL}	Pad-to-Y LOW			0.9		1.0		1.1		1.3		1.9	ns
Input Module Predicted Routing Delays¹													
t _{IRD1}	FO = 1 Routing Delay			2.9		3.4		3.8		4.5		6.3	ns
t _{IRD2}	FO = 2 Routing Delay			3.6		4.2		4.8		5.6		7.8	ns
t _{IRD3}	FO = 3 Routing Delay			4.4		5.0		5.7		6.7		9.4	ns
t _{IRD4}	FO = 4 Routing Delay			5.1		5.9		6.7		7.8		11.0	ns
t _{IRD8}	FO = 8 Routing Delay			8.0		9.26		10.5		12.6		17.3	ns
Global Clock Network													
t _{CKH}	Input LOW to HIGH	FO = 16		6.4		7.4		8.3		9.8		13.7	ns
		FO = 128		6.4		7.4		8.3		9.8		13.7	
t _{CKL}	Input HIGH to LOW	FO = 16		6.7		7.8		8.8		10.4		14.5	ns
		FO = 128		6.7		7.8		8.8		10.4		14.5	
t _{PWH}	Minimum Pulse Width HIGH	FO = 16	3.1		3.6		4.1		4.8		6.7		ns
		FO = 128	3.3		3.8		4.3		5.1		7.1		
t _{PWL}	Minimum Pulse Width LOW	FO = 16	3.1		3.6		4.1		4.8		6.7		ns
		FO = 128	3.3		3.8		4.3		5.1		7.1		
t _{CKSW}	Maximum Skew	FO = 16		0.6		0.6		0.7		0.8		1.2	ns
		FO = 128		0.8		0.9		1.0		1.2		1.6	

Table 35 • A40MX02 Timing Characteristics (Nominal 3.3 V Operation) (continued)
(Worst-Case Commercial Conditions, VCC = 3.0 V, T_J = 70°C)

Parameter / Description			–3 Speed		–2 Speed		–1 Speed		Std Speed		–F Speed		Units
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t _p	Minimum Period	FO = 16	6.5		7.5		8.5		10.1		14.1		ns
		FO = 128	6.8		7.8		8.9		10.4		14.6		
f _{MAX}	Maximum Frequency	FO = 16		113		105		96		83		50	MHz
		FO = 128		109		101		92		80		48	
TTL Output Module Timing ⁴													
t _{DLH}	Data-to-Pad HIGH			4.7		5.4		6.1		7.2		10.0	ns
t _{DHL}	Data-to-Pad LOW			5.6		6.4		7.3		8.6		12.0	ns
t _{ENZH}	Enable Pad Z to HIGH			5.2		6.0		6.8		8.1		11.3	ns
t _{ENZL}	Enable Pad Z to LOW			6.6		7.6		8.6		10.1		14.1	ns
t _{ENHZ}	Enable Pad HIGH to Z			11.1		12.8		14.5		17.1		23.9	ns
t _{ENLZ}	Enable Pad LOW to Z			8.2		9.5		10.7		12.6		17.7	ns
d _{TLH}	Delta LOW to HIGH			0.03		0.03		0.04		0.04		0.06	ns/pF
d _{THL}	Delta HIGH to LOW			0.04		0.04		0.05		0.06		0.08	ns/pF

Table 41 • A42MX16 Timing Characteristics (Nominal 3.3 V Operation) (continued)(Worst-Case Commercial Conditions, VCCA = 3.0 V, T_J = 70°C)

Parameter / Description			–3 Speed		–2 Speed		–1 Speed		Std Speed		–F Speed		Units
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Logic Module Sequential Timing ^{3, 4}													
t _{SUD}	Flip-Flop (Latch) Data Input Set-Up		0.5		0.5		0.6		0.7		0.9		ns
t _{HD}	Flip-Flop (Latch) Data Input Hold		0.0		0.0		0.0		0.0		0.0		ns
t _{SUENA}	Flip-Flop (Latch) Enable Set-Up		1.0		1.1		1.2		1.4		2.0		ns
t _{HENA}	Flip-Flop (Latch) Enable Hold		0.0		0.0		0.0		0.0		0.0		ns
t _{WCLKA}	Flip-Flop (Latch) Clock Active Pulse Width		4.8		5.3		6.0		7.1		9.9		ns
t _{WASYN}	Flip-Flop (Latch) Asynchronous Pulse Width		6.2		6.9		7.9		9.2		12.9		ns
t _A	Flip-Flop Clock Input Period		9.5		10.6		12.0		14.1		19.8		ns
t _{INH}	Input Buffer Latch Hold		0.0		0.0		0.0		0.0		0.0		ns
t _{INSU}	Input Buffer Latch Set-Up		0.7		0.8		0.9		1.01		1.4		ns
t _{OUTH}	Output Buffer Latch Hold		0.0		0.0		0.0		0.0		0.0		ns
t _{OUTSU}	Output Buffer Latch Set-Up		0.7		0.8		0.89		1.01		1.4		ns
f _{MAX}	Flip-Flop (Latch) Clock Frequency			129		117		108		94		56	MHz
Input Module Propagation Delays													
t _{INYH}	Pad-to-Y HIGH			1.5		1.6		1.9		2.2		3.1	ns
t _{INYL}	Pad-to-Y LOW			1.1		1.3		1.4		1.7		2.4	ns
t _{INGH}	G to Y HIGH			2.0		2.2		2.5		2.9		4.1	ns
t _{INGL}	G to Y LOW			2.0		2.2		2.5		2.9		4.1	ns
Input Module Predicted Routing Delays ²													
t _{IRD1}	FO = 1 Routing Delay			2.6		2.9		3.2		3.8		5.3	ns
t _{IRD2}	FO = 2 Routing Delay			2.9		3.2		3.7		4.3		6.1	ns
t _{IRD3}	FO = 3 Routing Delay			3.3		3.6		4.1		4.9		6.8	ns
t _{IRD4}	FO = 4 Routing Delay			3.6		4.0		4.6		5.4		7.6	ns
t _{IRD8}	FO = 8 Routing Delay			5.1		5.6		6.4		7.5		10.5	ns
Global Clock Network													
t _{CKH}	Input LOW to HIGH	FO = 32	4.4		4.8		5.5		6.5		9.0	ns	
		FO = 384	4.8		5.3		6.0		7.1		9.9	ns	
t _{CKL}	Input HIGH to LOW	FO = 32	5.3		5.9		6.7		7.8		11.0	ns	
		FO = 384	6.2		6.9		7.9		9.2		12.9	ns	
t _{PWH}	Minimum Pulse Width HIGH	FO = 32	5.7		6.3		7.1		8.4		11.8	ns	
		FO = 384	6.6		7.4		8.3		9.8		13.7	ns	

Table 44 • A42MX36 Timing Characteristics (Nominal 5.0 V Operation)(Worst-Case Commercial Conditions, VCCA = 4.75 V, T_J = 70°C)

Parameter / Description		–3 Speed		–2 Speed		–1 Speed		Std Speed		–F Speed		Units
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Logic Module Combinatorial Functions ¹												
t _{PD}	Internal Array Module Delay		1.3		1.5		1.7		2.0		2.7	ns
t _{PDD}	Internal Decode Module Delay		1.6		1.8		2.0		2.4		3.3	ns
Logic Module Predicted Routing Delays ²												
t _{RD1}	FO = 1 Routing Delay		0.9		1.0		1.2		1.4		2.0	ns
t _{RD2}	FO = 2 Routing Delay		1.3		1.4		1.6		1.9		2.7	ns
t _{RD3}	FO =3 Routing Delay		1.6		1.8		2.0		2.4		3.4	ns
t _{RD4}	FO = 4 Routing Delay		2.0		2.2		2.5		2.9		4.1	ns
t _{RD5}	FO = 8 Routing Delay		3.3		3.7		4.2		4.9		6.9	ns
t _{RDD}	Decode-to-Output Routing Delay		0.3		0.4		0.4		0.5		0.7	ns
Logic Module Sequential Timing ^{3, 4}												
t _{CO}	Flip-Flop Clock-to-Output		1.3		1.4		1.6		1.9		2.7	ns
t _{GO}	Latch Gate-to-Output		1.3		1.4		1.6		1.9		2.7	ns
t _{SUD}	Flip-Flop (Latch) Set-Up Time	0.3		0.3		0.4		0.5		0.7		ns
t _{HD}	Flip-Flop (Latch) Hold Time	0.0		0.0		0.0		0.0		0.0		ns
t _{RO}	Flip-Flop (Latch) Reset-to-Output		1.6		1.7		2.0		2.3		3.2	ns
t _{SUENA}	Flip-Flop (Latch) Enable Set-Up	0.7		0.8		0.9		1.0		1.4		ns
t _{HENA}	Flip-Flop (Latch) Enable Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{WCLKA}	Flip-Flop (Latch) Clock Active Pulse Width	3.3		3.7		4.2		4.9		6.9		ns
t _{WASYN}	Flip-Flop (Latch) Asynchronous Pulse Width	4.4		4.8		5.5		6.4		9.0		ns
Synchronous SRAM Operations												
t _{RC}	Read Cycle Time		6.8		7.5		8.5		10.0		14.0	ns
t _{WC}	Write Cycle Time		6.8		7.5		8.5		10.0		14.0	ns
t _{RCKHL}	Clock HIGH/LOW Time		3.4		3.8		4.3		5.0		7.0	ns
t _{RCO}	Data Valid After Clock HIGH/LOW		3.4		3.8		4.3		5.0		7.0	ns
t _{ADSU}	Address/Data Set-Up Time		1.6		1.8		2.0		2.4		3.4	ns
Synchronous SRAM Operations (continued)												
t _{ADH}	Address/Data Hold Time		0.0		0.0		0.0		0.0		0.0	ns
t _{RENSU}	Read Enable Set-Up		0.6		0.7		0.8		0.9		1.3	ns
t _{RENH}	Read Enable Hold		3.4		3.8		4.3		5.0		7.0	ns
t _{WENSU}	Write Enable Set-Up		2.7		3.0		3.4		4.0		5.6	ns
t _{WENH}	Write Enable Hold		0.0		0.0		0.0		0.0		0.0	ns
t _{BENS}	Block Enable Set-Up		2.8		3.1		3.5		4.1		5.7	ns
t _{BENH}	Block Enable Hold		0.0		0.0		0.0		0.0		0.0	ns

Table 45 • A42MX36 Timing Characteristics (Nominal 3.3 V Operation) (continued)(Worst-Case Commercial Conditions, VCCA = 3.0 V, T_J = 70°C)

Parameter / Description	–3 Speed		–2 Speed		–1 Speed		Std Speed		–F Speed		Units
	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t _{RD5} FO = 8 Routing Delay		4.6		5.2		5.8		6.9		9.6	ns
t _{RDD} Decode-to-Output Routing Delay		0.5		0.5		0.6		0.7		1.0	ns
Logic Module Sequential Timing^{3, 4}											
t _{CO} Flip-Flop Clock-to-Output		1.8		2.0		2.3		2.7		3.7	ns
t _{GO} Latch Gate-to-Output		1.8		2.0		2.3		2.7		3.7	ns
t _{SUD} Flip-Flop (Latch) Set-Up Time	0.4		0.5		0.6		0.7		0.9		ns
t _{HD} Flip-Flop (Latch) Hold Time	0.0		0.0		0.0		0.0		0.0		ns
t _{RO} Flip-Flop (Latch) Reset-to-Output		2.2		2.4		2.7		3.2		4.5	ns
t _{SUENA} Flip-Flop (Latch) Enable Set-Up	1.0		1.1		1.2		1.4		2.0		ns
t _{HENA} Flip-Flop (Latch) Enable Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{WCLKA} Flip-Flop (Latch) Clock Active Pulse Width	4.6		5.2		5.8		6.9		9.6		ns
t _{WASYN} Flip-Flop (Latch) Asynchronous Pulse Width	6.1		6.8		7.7		9.0		12.6		ns
Synchronous SRAM Operations											
t _{RC} Read Cycle Time		9.5		10.5		11.9		14.0		19.6	ns
t _{WC} Write Cycle Time		9.5		10.5		11.9		14.0		19.6	ns
t _{RCKHL} Clock HIGH/LOW Time		4.8		5.3		6.0		7.0		9.8	ns
t _{RCO} Data Valid After Clock HIGH/LOW		4.8		5.3		6.0		7.0		9.8	ns
t _{ADSU} Address/Data Set-Up Time	2.3		2.5		2.8		3.4		4.8		ns

Clock signal to shift the Boundary Scan Test (BST) data into the device. This pin functions as an I/O when "Reserve JTAG" is not checked in the Designer Software. BST pins are only available in A42MX24 and A42MX36 devices.

TDI, I/O Test Data In

Serial data input for BST instructions and data. Data is shifted in on the rising edge of TCK. This pin functions as an I/O when "Reserve JTAG" is not checked in the Designer Software. BST pins are only available in A42MX24 and A42MX36 devices.

TDO, I/O Test Data Out

Serial data output for BST instructions and test data. This pin functions as an I/O when "Reserve JTAG" is not checked in the Designer Software. BST pins are only available in A42MX24 and A42MX36 devices.

TMS, I/O Test Mode Select

The TMS pin controls the use of the IEEE 1149.1 Boundary Scan pins (TCK, TDI, TDO). In flexible mode when the TMS pin is set LOW, the TCK, TDI and TDO pins are boundary scan pins. Once the boundary scan pins are in test mode, they will remain in that mode until the internal boundary scan state machine reaches the "logic reset" state. At this point, the boundary scan pins will be released and will function as regular I/O pins. The "logic reset" state is reached 5 TCK cycles after the TMS pin is set HIGH. In dedicated test mode, TMS functions as specified in the IEEE 1149.1 specifications. IEEE JTAG specification recommends a 10k Ω pull-up resistor on the pin. BST pins are only available in A42MX24 and A42MX36 devices.

VCC, Supply Voltage

Input supply voltage for 40MX devices

VCCA, Supply Voltage

Supply voltage for array in 42MX devices

VCCI, Supply Voltage

Supply voltage for I/Os in 42MX devices

WD, I/O Wide Decode Output

When a wide decode module is used in a 42MX device this pin can be used as a dedicated output from the wide decode module. This direct connection eliminates additional interconnect delays associated with regular logic modules. To implement the direct I/O connection, connect an output buffer of any type to the output of the wide decode macro and place this output on one of the reserved WD pins.

Table 52 • PQ160

PQ160			
Pin Number	A42MX09 Function	A42MX16 Function	A42MX24 Function
58	VCCI	VCCI	VCCI
59	GND	GND	GND
60	VCCA	VCCA	VCCA
61	LP	LP	LP
62	I/O	I/O	TCK, I/O
63	I/O	I/O	I/O
64	GND	GND	GND
65	I/O	I/O	I/O
66	I/O	I/O	I/O
67	I/O	I/O	I/O
68	I/O	I/O	I/O
69	GND	GND	GND
70	NC	I/O	I/O
71	I/O	I/O	I/O
72	I/O	I/O	I/O
73	I/O	I/O	I/O
74	I/O	I/O	I/O
75	NC	I/O	I/O
76	I/O	I/O	I/O
77	NC	I/O	I/O
78	I/O	I/O	I/O
79	NC	I/O	I/O
80	GND	GND	GND
81	I/O	I/O	I/O
82	SDO, I/O	SDO, I/O	SDO, TDO, I/O
83	I/O	I/O	WD, I/O
84	I/O	I/O	WD, I/O
85	I/O	I/O	I/O
86	NC	VCCI	VCCI
87	I/O	I/O	I/O
88	I/O	I/O	WD, I/O
89	GND	GND	GND
90	NC	I/O	I/O
91	I/O	I/O	I/O
92	I/O	I/O	I/O
93	I/O	I/O	I/O
94	I/O	I/O	I/O

Table 54 • PQ240

PQ240	
Pin Number	A42MX36 Function
126	WD, I/O
127	I/O
128	VCCI
129	I/O
130	I/O
131	I/O
132	WD, I/O
133	WD, I/O
134	I/O
135	QCLKB, I/O
136	I/O
137	I/O
138	I/O
139	I/O
140	I/O
141	I/O
142	WD, I/O
143	WD, I/O
144	I/O
145	I/O
146	I/O
147	I/O
148	I/O
149	I/O
150	VCCI
151	VCCA
152	GND
153	I/O
154	I/O
155	I/O
156	I/O
157	I/O
158	I/O
159	WD, I/O
160	WD, I/O
161	I/O
162	I/O

Figure 47 • VQ100

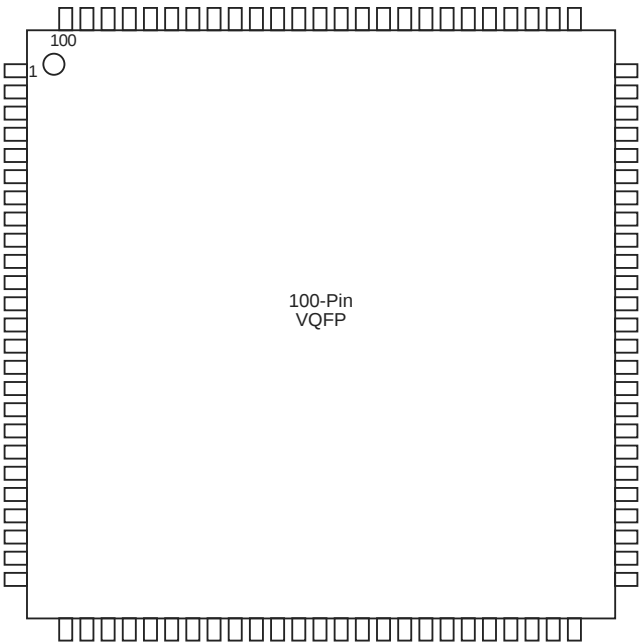


Table 56 • VQ100

VQ100		
Pin Number	A42MX09 Function	A42MX16 Function
1	I/O	I/O
2	MODE	MODE
3	I/O	I/O
4	I/O	I/O
5	I/O	I/O
6	I/O	I/O
7	GND	GND
8	I/O	I/O
9	I/O	I/O
10	I/O	I/O
11	I/O	I/O
12	I/O	I/O
13	I/O	I/O
14	VCCA	NC
15	VCCI	VCCI
16	I/O	I/O
17	I/O	I/O
18	I/O	I/O
19	I/O	I/O
20	GND	GND

Table 57 • TQ176

TQ176			
Pin Number	A42MX09 Function	A42MX16 Function	A42MX24 Function
158	CLKB, I/O	CLKB, I/O	CLKB, I/O
159	I/O	I/O	I/O
160	PRB, I/O	PRB, I/O	PRB, I/O
161	NC	I/O	WD, I/O
162	I/O	I/O	WD, I/O
163	I/O	I/O	I/O
164	I/O	I/O	I/O
165	NC	NC	WD, I/O
166	NC	I/O	WD, I/O
167	I/O	I/O	I/O
168	NC	I/O	I/O
169	I/O	I/O	I/O
170	NC	VCCI	VCCI
171	I/O	I/O	WD, I/O
172	I/O	I/O	WD, I/O
173	NC	I/O	I/O
174	I/O	I/O	I/O
175	DCLK, I/O	DCLK, I/O	DCLK, I/O
176	I/O	I/O	I/O

Figure 49 • CQ208

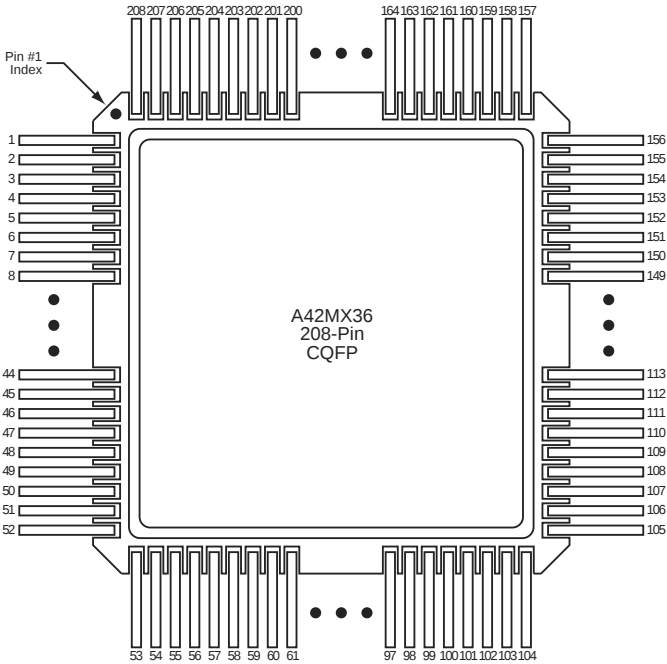


Table 58 • CQ208

CQ208	
Pin Number	A42MX36 Function
74	I/O
75	I/O
76	I/O
77	I/O
78	GND
79	VCCA
80	VCCI
81	I/O
82	I/O
83	I/O
84	I/O
85	WD, I/O
86	WD, I/O
87	I/O
88	I/O
89	I/O
90	I/O
91	QCLKB, I/O
92	I/O
93	WD, I/O
94	WD, I/O
95	I/O
96	I/O
97	I/O
98	VCCI
99	I/O
100	WD, I/O
101	WD, I/O
102	I/O
103	TDO, I/O
104	I/O
105	GND
106	VCCA
107	I/O
108	I/O
109	I/O
110	I/O

Table 60 • BG272

BG272	
Pin Number	A42MX36 Function
A6	I/O
A7	WD, I/O
A8	WD, I/O
A9	I/O
A10	I/O
A11	CLKA
A12	I/O
A13	I/O
A14	I/O
A15	I/O
A16	WD, I/O
A17	I/O
A18	I/O
A19	GND
A20	GND
B1	GND
B2	GND
B3	DCLK, I/O
B4	I/O
B5	I/O
B6	I/O
B7	WD, I/O
B8	I/O
B9	PRB, I/O
B10	I/O
B11	I/O
B12	WD, I/O
B13	I/O
B14	I/O
B15	WD, I/O
B16	I/O
B17	WD, I/O
B18	I/O
B19	GND
B20	GND
C1	I/O
C2	MODE

Table 60 • BG272

BG272	
Pin Number	A42MX36 Function
C3	GND
C4	I/O
C5	WD, I/O
C6	I/O
C7	QCLKC, I/O
C8	I/O
C9	I/O
C10	CLKB
C11	PRA, I/O
C12	WD, I/O
C13	I/O
C14	QCLKD, I/O
C15	I/O
C16	WD, I/O
C17	SDI, I/O
C18	I/O
C19	I/O
C20	I/O
D1	I/O
D2	I/O
D3	I/O
D4	I/O
D5	VCCI
D6	I/O
D7	I/O
D8	VCCA
D9	WD, I/O
D10	VCCI
D11	I/O
D12	VCCI
D13	I/O
D14	VCCI
D15	I/O
D16	VCCA
D17	GND
D18	I/O
D19	I/O